

The TQTHL211XXV is a high power TVS, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive lines. The TQTHL211XXV Series complies with the IEC 610002 (ESD) standard with  $\pm 30\text{kV}$  air and  $\pm 30\text{kV}$  contact discharge. It is assembled into a 3pin DFN2020-3 package. The leads are finished with NiPdAu. Each device will protect one line. The combination of small size, and high surge capability makes them ideal for use in applications such as cellular phones, LCD displays, USB, and multimedia card interfaces.

## Features

- Protects one I/O lines
- Working voltages :12V、14V、17V、24V
- Low leakage current
- Response Time is  $< 1\text{ ns}$
- Meets MSL 1 Requirements
- Solid-state silicon avalanche technology
- ROHS compliant
- TECH CHIP technology

## Main applications

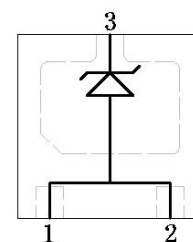
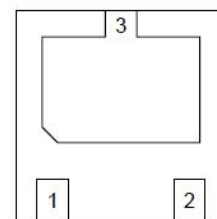
- Power Management
- Industrial Application
- Power Supply Protection

## Protection solution to meet

- IEC61000-4-2 (ESD)  $\pm 30\text{kV}$  (air),  $\pm 30\text{kV}$  (contact)
- IEC61000-4-4 (EFT) 40A (5/50ns)



**DFN2020-3L**



## Ordering Information

Device	Mark	Qty per Reel	Reel Size
TQTHL21112V	12P	3000	7 Inch
TQTHL21114V	14P	3000	7 Inch
TQTHL21117V	17P	3000	7 Inch
TQTHL21124V	T24	3000	7 Inch

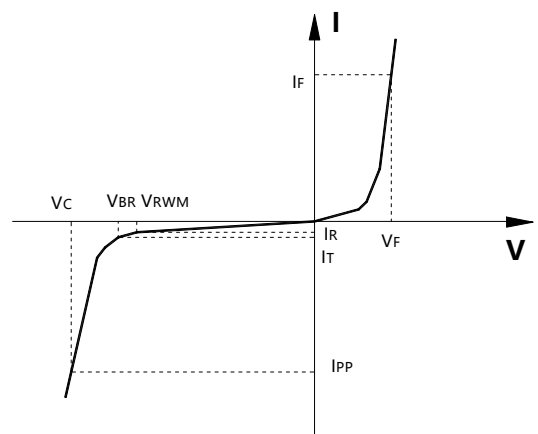
Maximum ratings (Temp=25°C Unless Otherwise Specified)			
Parameter	Symbol	Value	Unit
ESD Rating per IEC61000-4-2:	Contact	30	KV
	Air	30	
Lead Soldering Temperature	T <sub>L</sub>	260 (10 sec.)	°C
Operating Temperature Range	T <sub>J</sub>	-55 ~ 150	°C
Storage Temperature Range	T <sub>STG</sub>	-55 ~ 150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

\*Other voltages may be available upon request.

1. Non-repetitive current pulse, per Figure 1.

Symbol	Parameter
V <sub>RWM</sub>	Working Peak Reverse Voltage
V <sub>BR</sub>	Breakdown Voltage @ I <sub>T</sub>
V <sub>C</sub>	Clamping Voltage @ I <sub>PP</sub>
I <sub>T</sub>	Test Current
I <sub>RM</sub>	Leakage current at V <sub>RWM</sub>
I <sub>PP</sub>	Peak pulse current
C <sub>O</sub>	Off-state Capacitance
C <sub>J</sub>	Junction Capacitance



## TQTHL21112V

Electrical characteristics (Temp=25°C Unless Otherwise Specified)						
Sym bol	Parameter	Conditions	Min.	Typ.	Max.	Units
V <sub>RWM</sub>	Reverse Working Voltage	Pin 3 to pin 1,2			12	V
V <sub>BR</sub>	Reverse Breakdown Voltage	I <sub>T</sub> = 1mA, Pin 3 to pin 1,2	13.5			V
I <sub>R</sub>	Reverse Leakage Current	V <sub>RWM</sub> = 12V, Pin 3 to pin 1,2			1	μA
V <sub>C</sub>	Clamping Voltage	I <sub>PP</sub> = 50A, tp = 8/20μs, Pin 3 to pin 1,2		19		V
		I <sub>PP</sub> = 170A, tp = 8/20μs,		24.5	29	V

		Pin 3 to pin 1,2				
C <sub>J</sub>	Junction Capacitance	V <sub>R</sub> = 0V, f = 1MHz, Pin 3 to pin 1,2		1.3		nF
I <sub>PP</sub>	Peak Pulse Current	tp=8/20μs waveform			190	A
P <sub>pp</sub>	Peak Pulse Power	tp=8/20μs waveform		4500		W

## BVSTHL21114V

Electrical characteristics ( Temp=25°C Unless Otherwise Specified)						
Sym bol	Parameter	Conditions	Min.	Typ.	Max.	Units
V <sub>RWM</sub>	Reverse Working Voltage	Pin 3 to pin 1,2			14	V
V <sub>BR</sub>	Reverse Breakdown Voltage	I <sub>T</sub> = 1mA, Pin 3 to pin 1,2	15.2			V
I <sub>R</sub>	Reverse Leakage Current	V <sub>RWM</sub> =14V, Pin 3 to pin 1,2			1	μA
V <sub>C</sub>	Clamping Voltage	I <sub>PP</sub> = 50A, tp =8/20μs, Pin 3 to pin 1,2		21		V
		I <sub>PP</sub> =160A, tp =8/20μs, Pin 3 to pin 1,2		27.5	31	V
C <sub>J</sub>	Junction Capacitance	V <sub>R</sub> = 0V, f = 1MHz, Pin 3 to pin 1,2		1.1		nF
I <sub>PP</sub>	Peak Pulse Current	tp=8/20μs waveform			170	A
P <sub>pp</sub>	Peak Pulse Power	tp=8/20μs waveform		4500		W

## BVSTHL21117V

Electrical characteristics ( Temp=25°C Unless Otherwise Specified)						
Sym bol	Parameter	Conditions	Min.	Typ.	Max.	Units
V <sub>RWM</sub>	Reverse Working Voltage	Pin 3 to pin 1,2			17	V
V <sub>BR</sub>	Reverse Breakdown Voltage	I <sub>T</sub> = 1mA, Pin 3 to pin 1,2	18.2			V
I <sub>R</sub>	Reverse Leakage Current	V <sub>RWM</sub> =17V, Pin 3 to pin 1,2			1	μA
V <sub>C</sub>	Clamping Voltage	I <sub>PP</sub> = 50A, tp =8/20μs, Pin 3 to pin 1,2		26		V
		I <sub>PP</sub> =130A, tp =8/20μs, Pin 3 to pin 1,2		30	36	V
C <sub>J</sub>	Junction Capacitance	V <sub>R</sub> = 0V, f = 1MHz,		0.95		nF

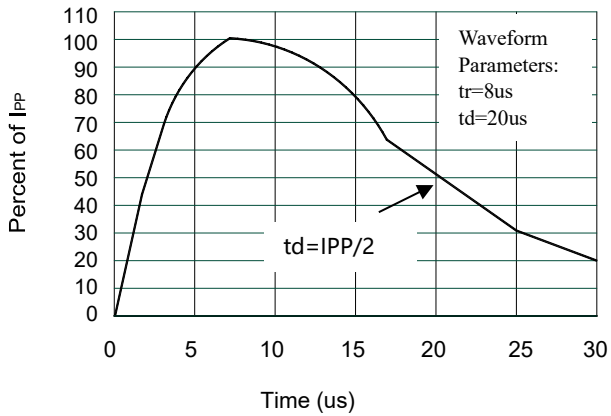
		Pin 3 to pin 1,2				
I <sub>PP</sub>	Peak Pulse Current	tp=8/20μs waveform			150	A
P <sub>pp</sub>	Peak Pulse Power	tp=8/20μs waveform		4500		W

## BVSTHL21124V

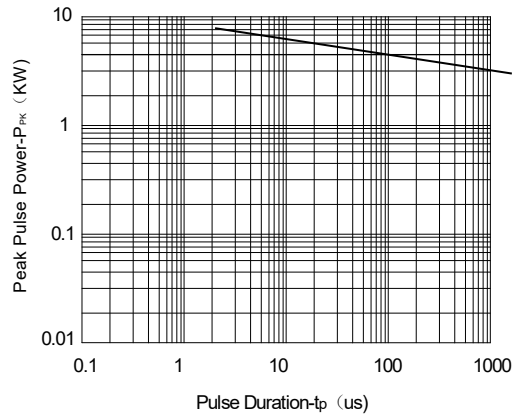
Electrical characteristics ( Temp=25°C Unless Otherwise Specified)						
Sym bol	Parameter	Conditions	Min.	Typ.	Max.	Units
V <sub>RWM</sub>	Reverse Working Voltage	Pin 3 to pin 1,2			24	V
V <sub>BR</sub>	Reverse Breakdown Voltage	I <sub>T</sub> = 1mA, Pin 3 to pin 1,2	25			V
I <sub>R</sub>	Reverse Leakage Current	V <sub>RWM</sub> =24V, Pin 3 to pin 1,2			1	μA
V <sub>C</sub>	Clamping Voltage	I <sub>PP</sub> = 50A, tp =8/20μs, Pin 3 to pin 1,2		26		V
		I <sub>PP</sub> =150A, tp =8/20μs, Pin 3 to pin 1,2		29	35	V
C <sub>J</sub>	Junction Capacitance	V <sub>R</sub> = 0V, f = 1MHz, Pin 3 to pin 1,2		0.74		nF
I <sub>PP</sub>	Peak Pulse Current	tp=8/20μs waveform			200	A
P <sub>pp</sub>	Peak Pulse Power	tp=8/20μs waveform		5500		W

*Junction capacitance is measured in VR=0V,F=1MHz*

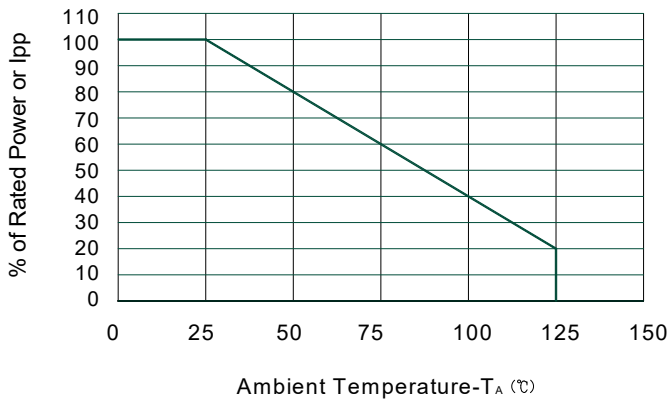
## Typical electrical characterist applications



**Pulse Waveform**



**Non-Repetitive Peak Pulse Power vs. Pulse Time**



**Power Derating Curve**

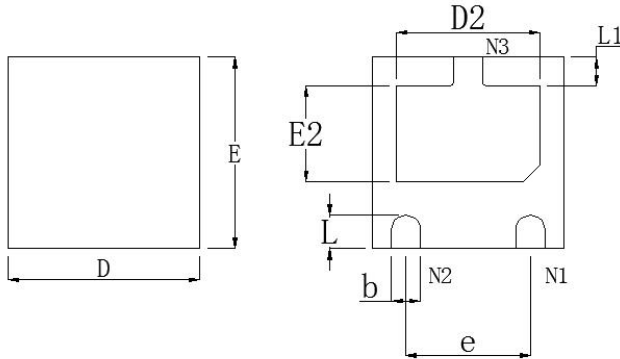
## Package Information

## DFN2020

### Mechanical Data

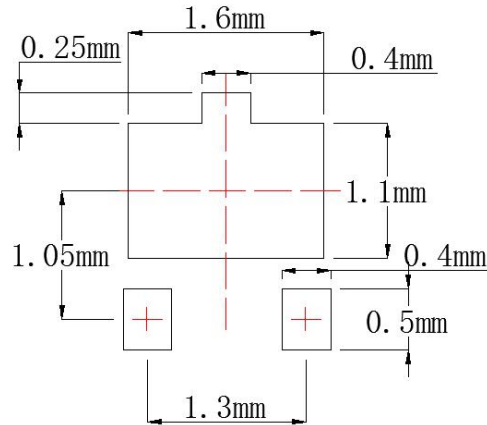
Case:DFN2020

Case Material: Molded Plastic. UL Flammability



DIM	Millimeters		
	Min	Nom	Max
A	0.50	0.55	0.60
A1	0.00	-	0.05
A3	0.15 REF.		
D	1.95	2.00	2.05
E	1.95	2.00	2.05
b	0.25	0.30	0.35
L	0.30	0.35	0.40
L1	0.25	0.30	0.35
D2	1.35	1.50	1.60
E2	0.85	1.00	1.10
e	1.30 BSC		

### Recommended Pad outline



### DISCLAIMER



# TQTHL211XXV

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